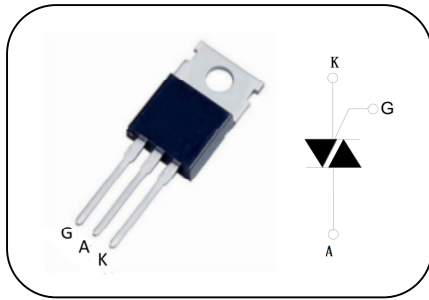


**Features:**

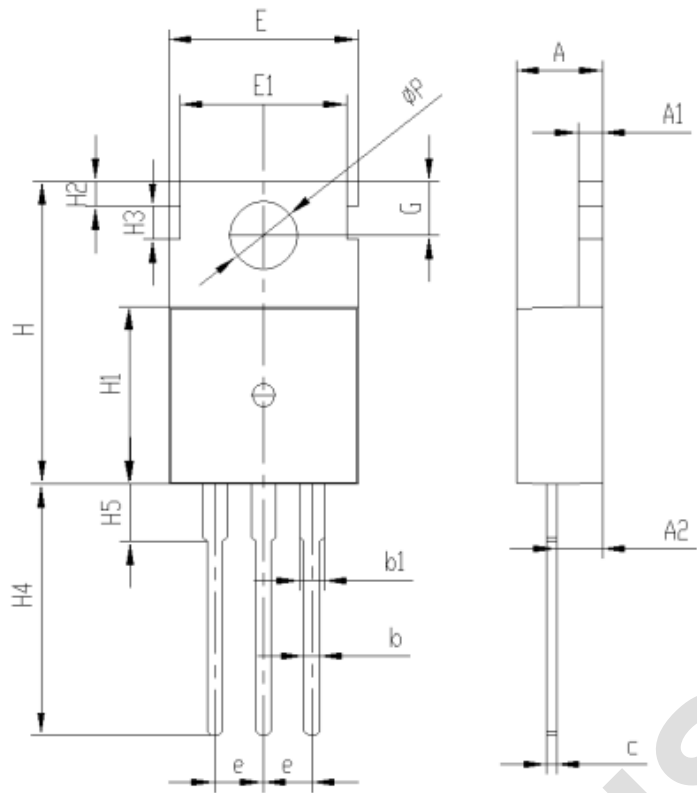
Two anti-parallel thyristors on one
Si-wafer
Hermetic metal cases with ceramic
insulators
Capsule packages for double sided
cooling

Typical Applications

High power industrial and power
transmission
DC and AC motor control
AC controllers

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _J (C)	VALUE			UNIT
				Min	Type	Max	
I _{T(RMS)}	RMS current	full sine wave Single side cooled, T _C =25°C	25			24	A
V _{DRM} V _{R RM}	Repetitive peak reverse voltage	V _{DRM} tp=10ms V _{DSM} = V _{DRM} +100V	150			800	V
I _{DRM}	Repetitive peak current	V _{DM} = V _{DRM}	25		5		μA
I _{RRM}	Repetitive peak current	V _{RM} = V _{RRM}			2		mA
I _{TSM}	Surge on-state current	10ms half sine wave	25			240	A
I ² t	I ² T for fusing coordination	V _R =0.6V _{RRM}				288	A ² s
V _{TM}	Peak on-state voltage	I _{TM} =48A, tp=380μs	25		1.45		V
dv/dt	Critical rate of rise of off-state voltage (dv/dt)/c	V _{DM} =0.67V _{DRM} gate open	125	500			V/μs
		Without snubber	125	20			V/μs
di/dt	Critical rate of rise of on-state current	I _G =2*I _{GT}	25	100			A/μs
I _{GT}	Gate trigger current	V _D =12V _{DC} , R _L =33Ω I - II -III	25			35	mA
V _{GT}	Gate trigger voltage					1.3	V
V _{GD}	Non-trigger gate voltage	V _D =V _{DRM} , R _L =33Ω	125	0.2			
I _L	Latching current	I _G =1.2I _{GT}	25			80	mA
						100	mA
I _H	Holding current	V _D =12V _{DC} , R _L =33Ω	25	10			mA
I _{GM}	Peak gate current	tp=20μs	25			8	A
P _{GM}	Peak gate power	tp=20μs	25			10	w
P _{G(AV)}	Average gate power dissipation		25			2	w
R _{th(j-c)}	Thermal resistance Junction to case	Single side cooled				0.5	C /W
T _J	Operating Junction temperature			-40		125	C
T _{stg}	Stored temperature			-40		150	C
Outline	TO-220C						

Outline:



Symbol	Dimensions(millimeters)	
	Min.	Max.
A	4.30	4.70
A1	1.17	1.37
A2	2.20	2.60
b	0.60	1.00
b1	1.17	1.37
b2	1.90	2.30
c	0.30	0.70
e	2.34	2.74
E	9.70	10.1
E1	8.50	8.90
H	15.5	15.9
H1	9.00	9.40
H2	1.10	1.50
H3	1.50	1.90
H4	12.58	13.58
H5	2.80	3.20
G	2.60	3.00
ΦP	3.40	3.80